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### November 2013

# FQP30N06L

# N-Channel QFET<sup>®</sup> MOSFET 60 V, 32 A, 35 m $\Omega$

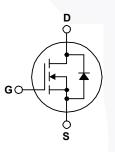
## Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

### Features

- 32 A, 60 V,  $R_{DS(on)}$  = 35 m $\Omega$  (Max.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 16 A
- Low Gate Charge (Typ. 15 nC)
- Low Crss (Typ. 50 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





# Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

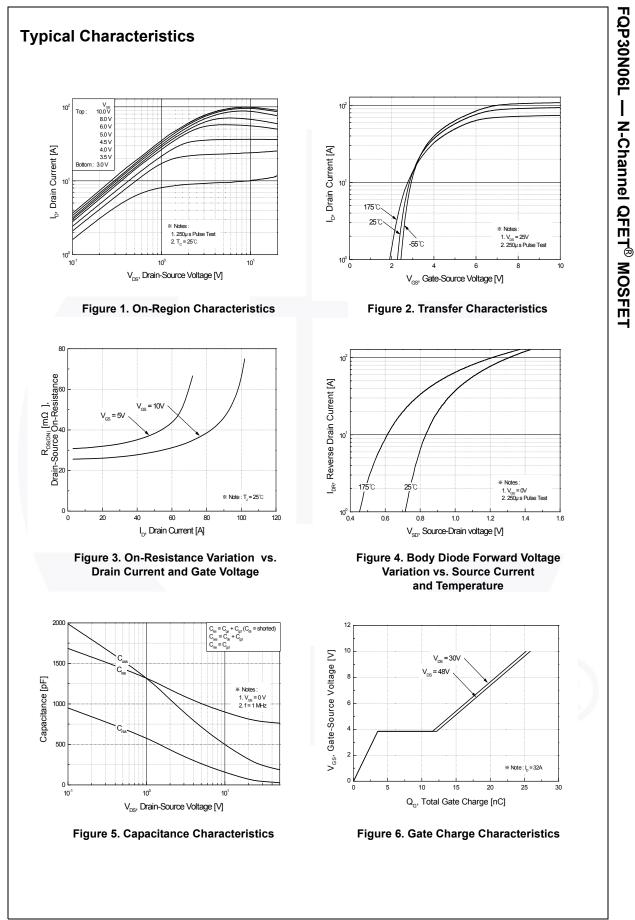
Symbol	Parameter		FQP30N06L	Unit
V <sub>DSS</sub>	Drain-Source Voltage		60	V
I <sub>D</sub>	Drain Current - Continuous ( $T_C = 25^\circ$	C)	32	A
	- Continuous (T <sub>C</sub> = 100	°C)	22.6	Α
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	128	Α
V <sub>GSS</sub>	Gate-Source Voltage		± 20	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	350	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	32	A
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	7.9	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	7.0	V/ns
P <sub>D</sub>	Power Dissipation ( $T_C = 25^{\circ}C$ )		79	W
	- Derate above 25°C		0.53	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C

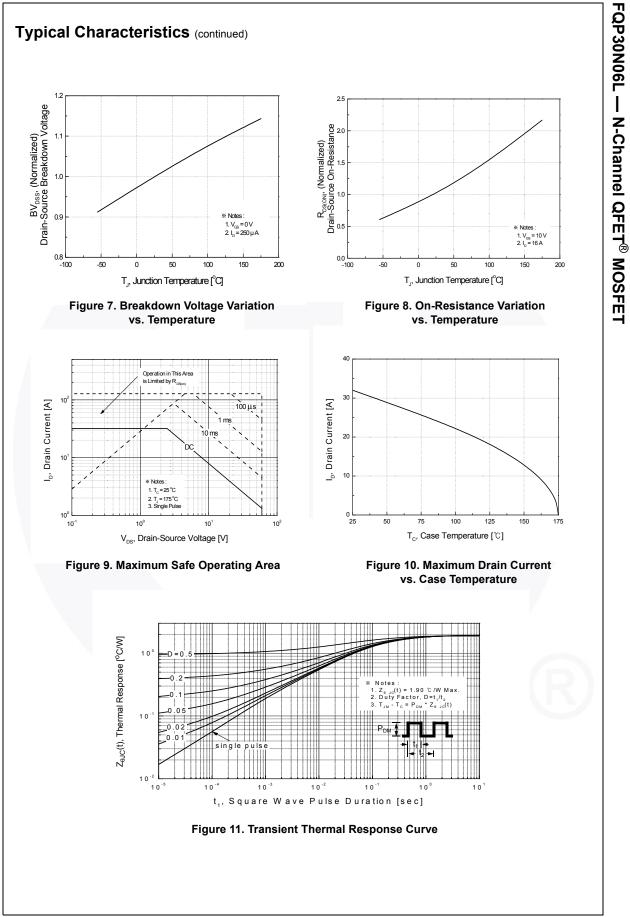
# **Thermal Characteristics**

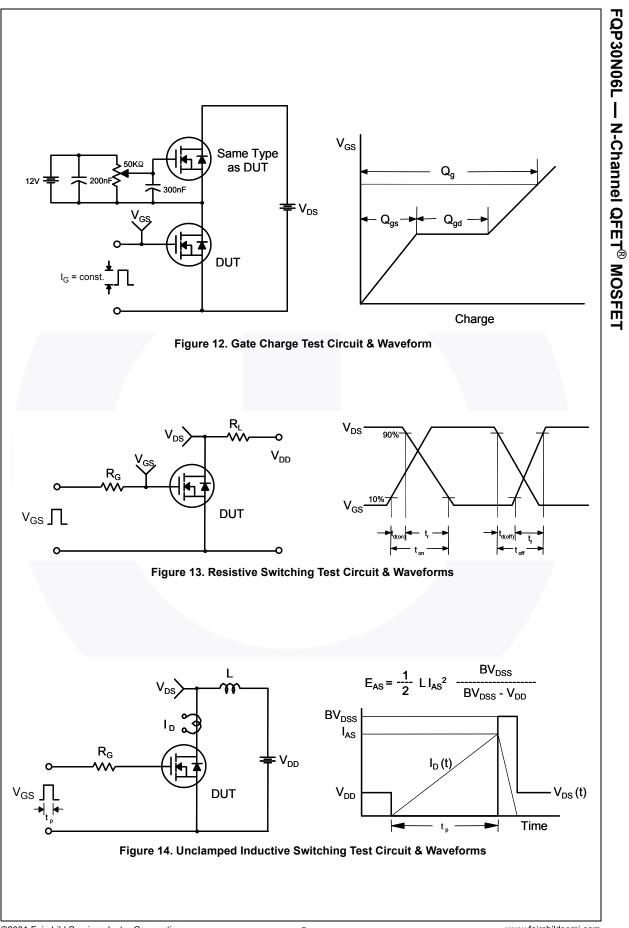
Symbol	Parameter	FQP30N06L	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.90	°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

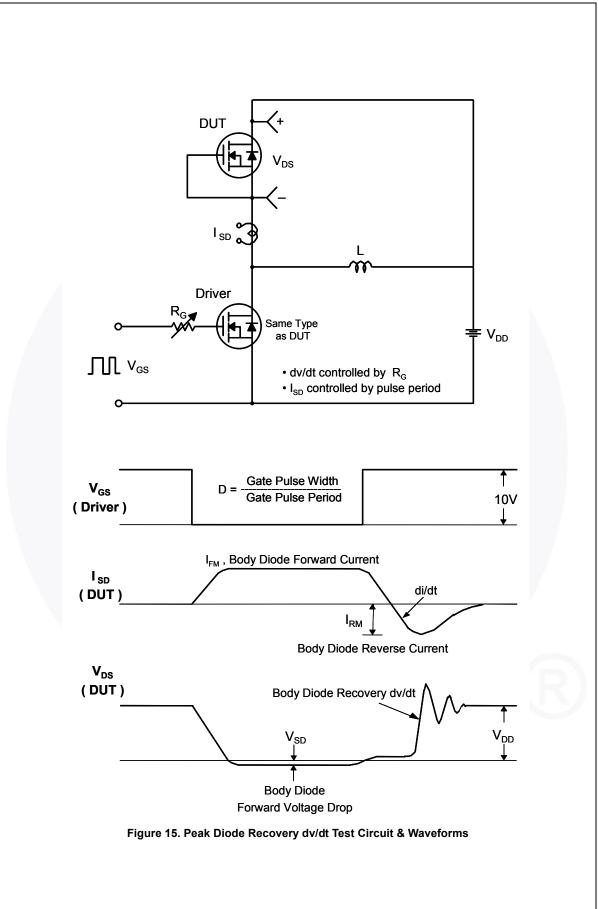
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ransconductance		V <sub>DS</sub> = 25 V, I <sub>D</sub> = 16 A			24		S
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,					210	430	ns
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2			(Note 4)		110	230	ns
e Charge		V <sub>DS</sub> = 48 V I <sub>D</sub> = 32 A			15	20	nC
					3.5		nC
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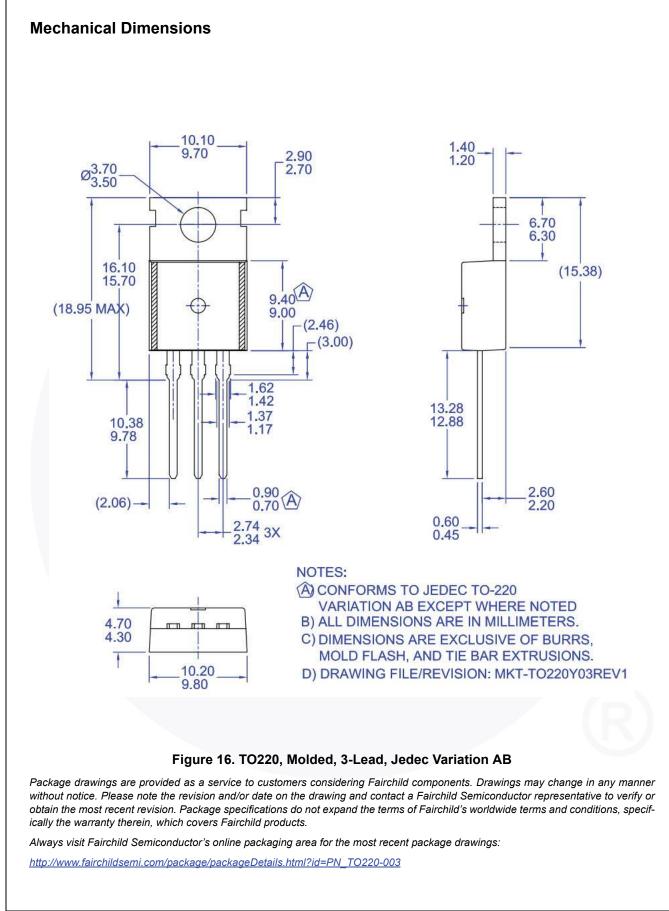
2. L = 400 µm <sub>1</sub>g = 52 ×  $_{VDP}$  = 25 ×  $_{SI}$  starting T = 25 °C. 3. I<sub>SD</sub> = 32 Å, didt ≤ 300 Å/us, V<sub>DD</sub> ≤ BV<sub>DSS</sub> starting T<sub>J</sub> = 25 °C. 4.Essentially independent of operating temperature. FQP30N06L — N-Channel QFET<sup>®</sup> MOSFET













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